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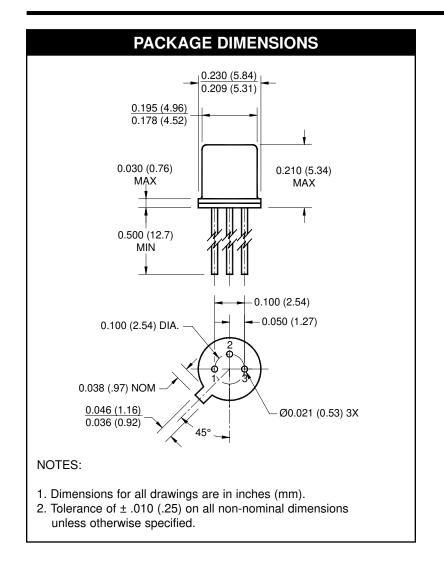
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

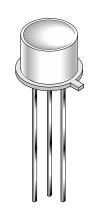


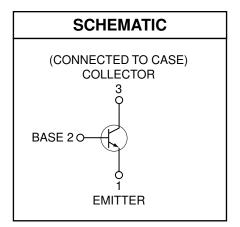




L14C1 L14C2







DESCRIPTION

The L14C1/L14C2 are silicon phototransistors mounted in a wide angle, TO-18 package.

FEATURES

- · Hermetically sealed package
- · Wide reception angle



L14C1 L14C2

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise specified)								
Parameter	Symbol	Rating	Unit					
Operating Temperature	T _{OPR}	-65 to +125	°C					
Storage Temperature	T _{STG}	-65 to +150	°C					
Soldering Temperature (Iron)(3,4,5 and 6)	T _{SOL-I}	240 for 5 sec	°C					
Soldering Temperature (Flow)(3,4 and 6)	T _{SOL-F}	260 for 10 sec	°C					
Collector to Emitter Breakdown Voltage	V _{CEO}	50	V					
Collector to Base Breakdown Voltage	V_{CBO}	50	V					
Emitter to Base Breakdwon Voltage	V _{EBO}	7	V					
Power Dissipation (T _A = 25°C) ⁽¹⁾	P _D	300	mW					
Power Dissipation ($T_C = 25^{\circ}C$) ⁽²⁾	P _D	600	mW					

NOTE:

- 1. Derate power dissipation linearly 3.00 mW/°C above 25°C ambient.
- 2. Derate power dissipation linearly 6.00 mW/°C above 25°C case.
- 3. RMA flux is recommended.
- 4. Methanol or isopropyl alcohols are recommended as cleaning agents.
- 5. Soldering iron tip 1/16" (1.6mm) minimum from housing.
- 6. As long as leads are not under any stress or spring tension.
- 7. Light source is a GaAs LED emitting light at a peak wavelength of 940 nm.
- 8. Figure 1 and figure 2 use light source of tungsten lamp at 2870°K color temperature. A GaAs source of 3.0 mW/cm² is approximately equivalent to a tungsten source, at 2870°K, of 10 mW/cm².

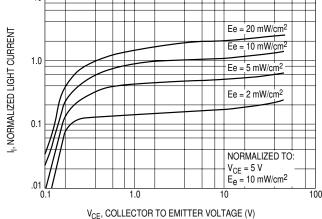
ELECTRICAL / OPTICAL CHARACTERISTICS (TA =25°C) (All measurements made under pulse conditions)								
PARAMETER	TEST CONDITIONS	SYMBOL	MIN	TYP	MAX	UNITS		
Collector-Emitter Breakdown	$I_{\rm C} = 10 \text{ mA}, Ee = 0$	BV _{CEO}	50		_	V		
Emitter-Base Breakdown	I _E = 100 μA, Ee = 0	BV _{EBO}	7.0			V		
Collector-Base Breakdown	$I_{\rm C} = 100 \ \mu A, \ {\rm Ee} = 0$	BV _{CBO}	50			V		
Collector-Emitter Leakage	V _{CE} = 20 V, Ee = 0	I _{CEO}	_		100	nA		
Reception Angle at 1/2 Sensitivity		θ		±40		Degrees		
On-State Collector Current L14C1	Ee = 0.5 mW/cm ² , $V_{CE} = 5 V^{(7,8)}$	I _{C(ON)}	.16		_	mA		
On-State Collector Current L14C2	Ee = 0.5 mW/cm ² , $V_{CE} = 5 V^{(7,8)}$	I _{C(ON)}	.08		_	mA		
On-State Collector Current L14C2	Ee = 1.0 mW/cm ² , $V_{CE} = 5 V^{(7,8)}$	I _{C(ON)}	.16		_	mA		
Turn-On Time	$I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega$	t _{on}		5		μs		
Turn-Off Time	$I_C = 2$ mA, $V_{CC} = 10$ V, $R_L = 100$ Ω	t _{off}		5		μs		
Saturation Voltage	$I_{\rm C} = 0.40 \text{ mA}, \text{ Ee} = 6.0 \text{ mW/cm}^{2(7,8)}$	V _{CE(SAT)}	_		0.40	V		

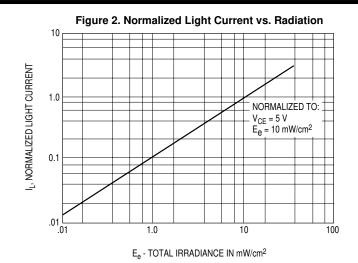


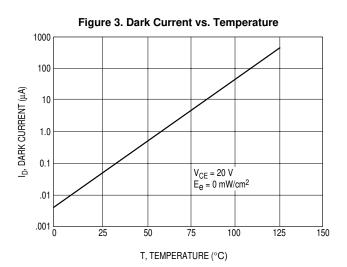
L14C1 L14C2

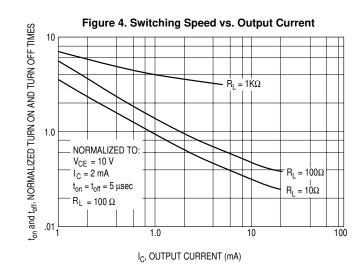
 $Ee = 20 \text{ mW/cm}^2$ $Ee = 10 \text{ mW/cm}^2$

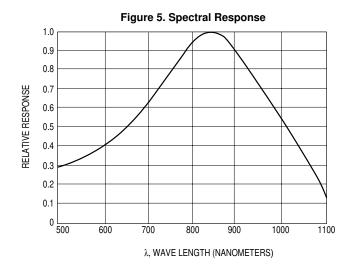
Figure 1. Light Current vs. Collector to Emitter Voltage

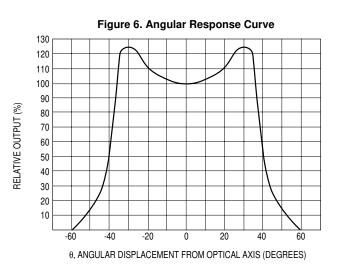














L14C1 L14C2

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